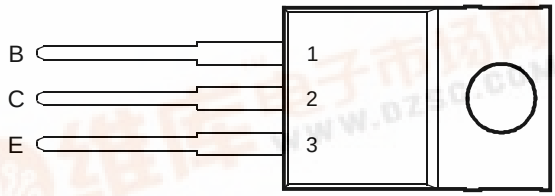
BD543, BD543A, BD543B, BD543C
NPN SILICON POWER TRANSISTORS

 JUNE 1973 - REVISED MARCH 1997

- **Designed for Complementary Use with the BD544 Series**
- **70 W at 25°C Case Temperature**
- **8 A Continuous Collector Current**
- **10 A Peak Collector Current**
- **Customer-Specified Selections Available**

TO-220 PACKAGE
(TOP VIEW)



Pin 2 is in electrical contact with the mounting base.

MDTRACA

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING		SYMBOL	VALUE	UNIT
Collector-base voltage (I_E = 0)	BD543	V_{CBO}	40	V
	BD543A		60	
	BD543B		80	
	BD543C		100	
Collector-emitter voltage (I_B = 0)	BD543	V_{CEO}	40	V
	BD543A		60	
	BD543B		80	
	BD543C		100	
Emitter-base voltage		V_{EBO}	5	V
Continuous collector current		I_C	8	A
Peak collector current (see Note 1)		I_{CM}	10	A
Continuous device dissipation at (or below) 25°C case temperature (see Note 2)		P_{tot}	70	W
Continuous device dissipation at (or below) 25°C free air temperature (see Note 3)		P_{tot}	2	W
Operating free air temperature range		T_A	-65 to +150	°C
Operating junction temperature range		T_j	-65 to +150	°C
Storage temperature range		T_{stg}	-65 to +150	°C
Lead temperature 3.2 mm from case for 10 seconds		T_L	260	°C

NOTES: 1. This value applies for $t_p \leq 0.3$ ms, duty cycle ≤ 10%.
2. Derate linearly to 150°C case temperature at the rate of 0.56 W/°C.
3. Derate linearly to 150°C free air temperature at the rate of 16 mW/°C.

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electrical characteristics at 25°C case temperature

PARAMETER		TEST CONDITIONS			MIN	TYP	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C = 30 mA (see Note 4)	I_B = 0	BD543	40			V
				BD543A	60			
				BD543B	80			
				BD543C	100			
I_{CES}	Collector-emitter cut-off current	V_{CE} = 40 V	V_{BE} = 0	BD543			0.4	mA
		V_{CE} = 60 V	V_{BE} = 0	BD543A			0.4	
		V_{CE} = 80 V	V_{BE} = 0	BD543B			0.4	
		V_{CE} = 100 V	V_{BE} = 0	BD543C			0.4	
I_{CEO}	Collector cut-off current	V_{CE} = 30 V	I_B = 0	BD543/543A			0.7	mA
		V_{CE} = 60 V	I_B = 0	BD543B/543C			0.7	
I_{EBO}	Emitter cut-off current	V_{EB} = 5 V	I_C = 0				1	mA
h_{FE}	Forward current transfer ratio	V_{CE} = 4 V	I_C = 1 A		60			
		V_{CE} = 4 V	I_C = 3 A	(see Notes 4 and 5)	40			
		V_{CE} = 4 V	I_C = 5 A		15			
$V_{CE(sat)}$	Collector-emitter saturation voltage	I_B = 0.3 A	I_C = 3 A				0.5	V
		I_B = 1 A	I_C = 5 A	(see Notes 4 and 5)			0.5	
		I_B = 1.6 A	I_C = 8 A				1	
V_{BE}	Base-emitter voltage	V_{CE} = 4 V	I_C = 5 A	(see Notes 4 and 5)			1.4	V
h_{fe}	Small signal forward current transfer ratio	V_{CE} = 10 V	I_C = 0.5 A	f = 1 kHz	20			
$\|h_{fe}\|$	Small signal forward current transfer ratio	V_{CE} = 10 V	I_C = 0.5 A	f = 1 MHz	3			

NOTES: 4. These parameters must be measured using pulse techniques, t_p = 300 µs, duty cycle ≤ 2%.
5. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

thermal characteristics

PARAMETER		MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to case thermal resistance			1.79	°C/W
$R_{\theta JA}$	Junction to free air thermal resistance			62.5	°C/W

resistive-load-switching characteristics at 25°C case temperature

PARAMETER		TEST CONDITIONS †			MIN	TYP	MAX	UNIT
t_{on}	Turn-on time	I_C = 6 A	$I_{B(on)}$ = 0.6 A	$I_{B(off)}$ = -0.6 A		0.6		µs
t_{off}	Turn-off time	$V_{BE(off)}$ = -4 V	R_L = 5 Ω	t_p = 20 µs, dc ≤ 2%		1		µs

† Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.

TYPICAL CHARACTERISTICS

TYPICAL DC CURRENT GAIN
vs
COLLECTOR CURRENT

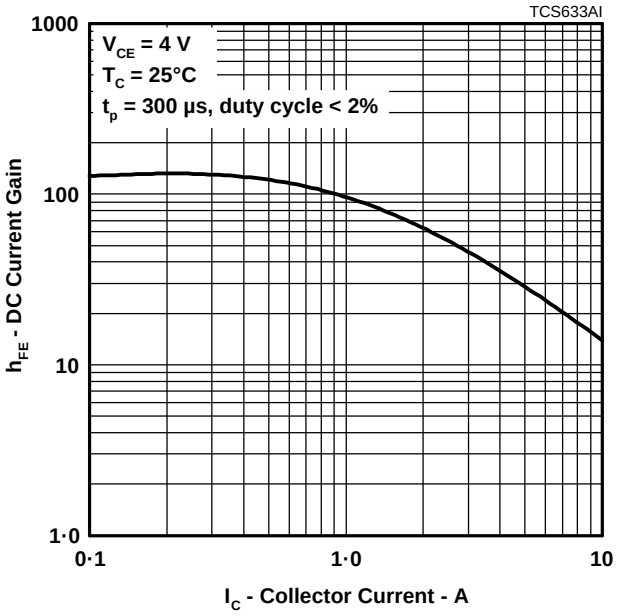


Figure 1.

COLLECTOR-EMITTER SATURATION VOLTAGE
vs
BASE CURRENT

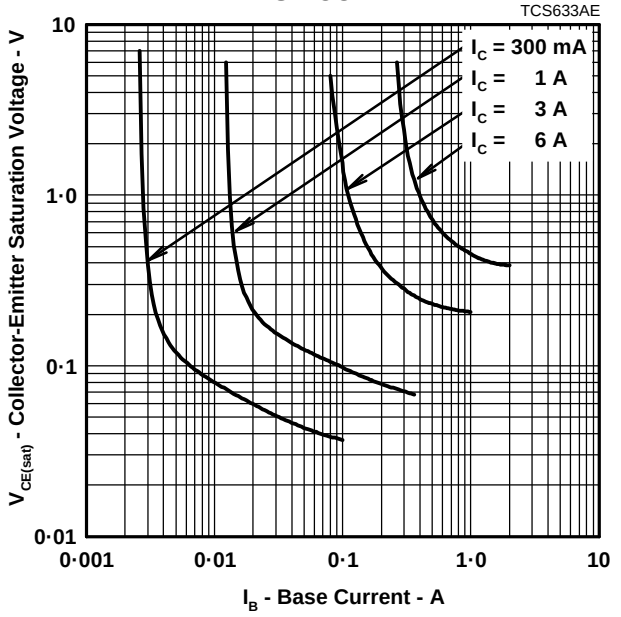


Figure 2.

BASE-EMITTER VOLTAGE
vs
COLLECTOR CURRENT

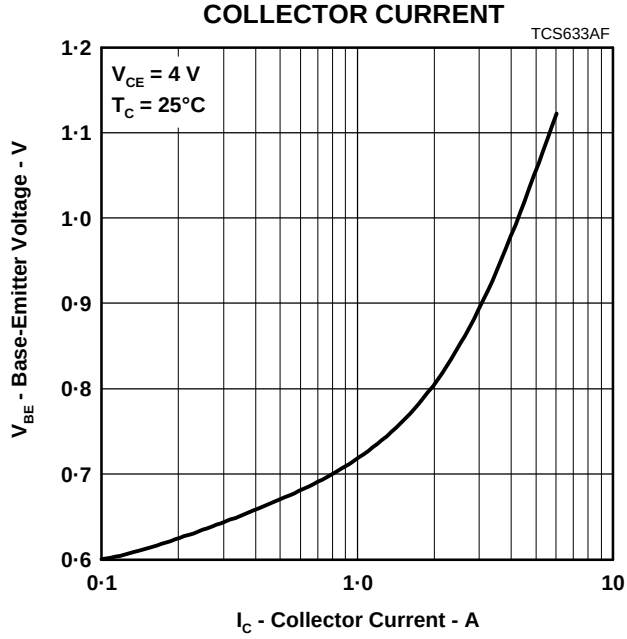


Figure 3.

MAXIMUM SAFE OPERATING REGIONS

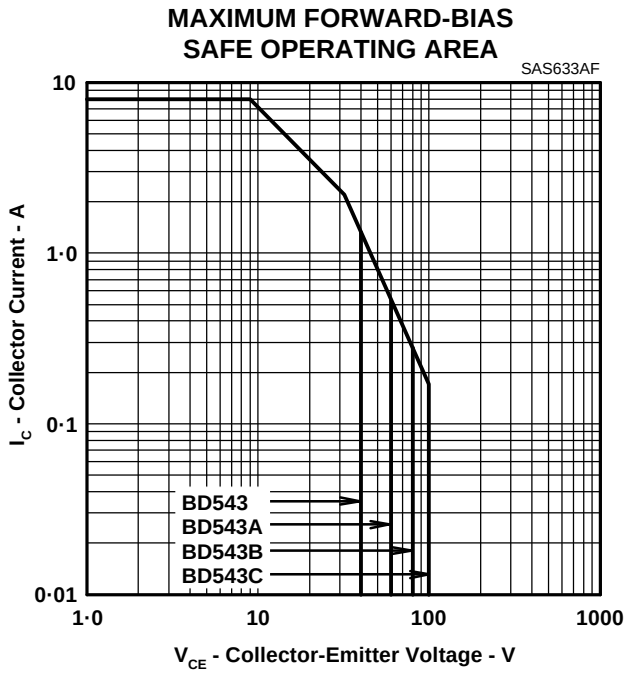


Figure 4.

THERMAL INFORMATION

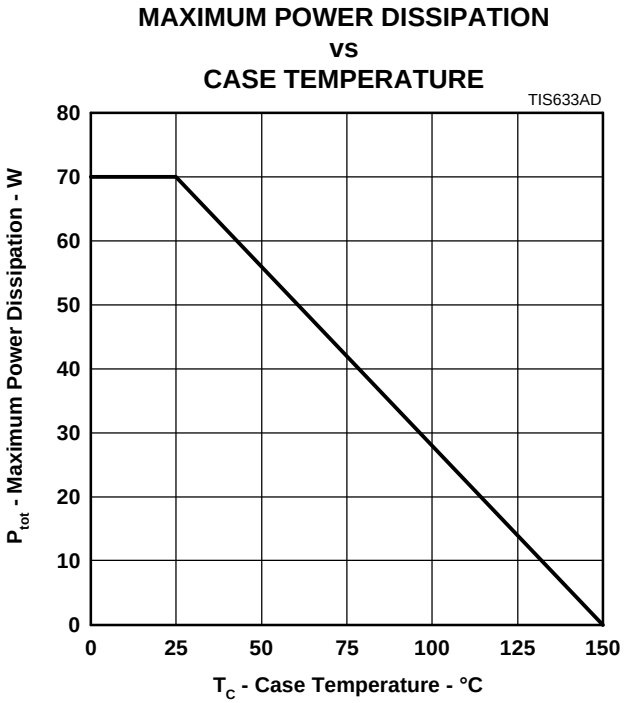
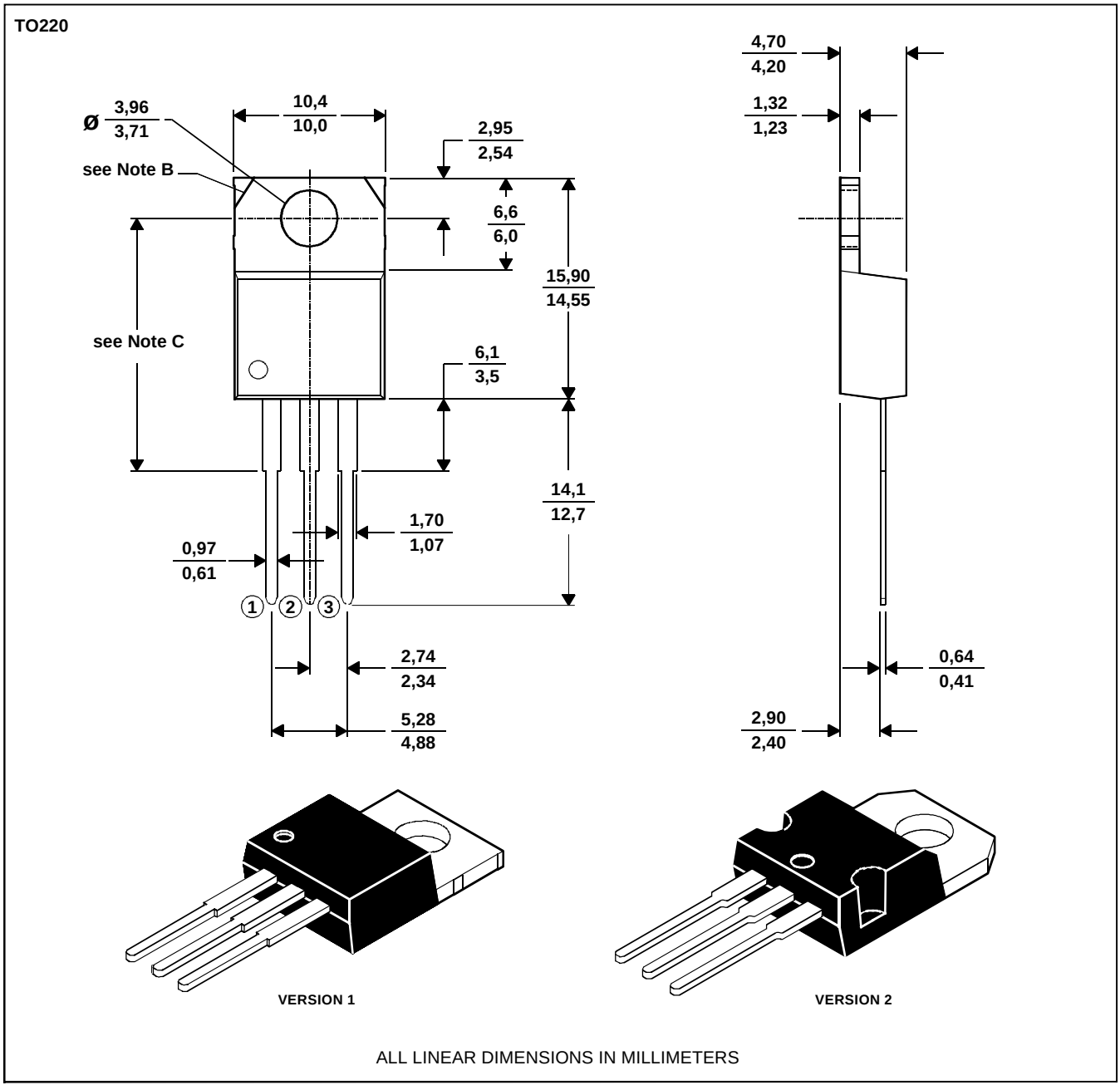


Figure 5.

MECHANICAL DATA

TO-220
3-pin plastic flange-mount package

This single-in-line package consists of a circuit mounted on a lead frame and encapsulated within a plastic compound. The compound will withstand soldering temperature with no deformation, and circuit performance characteristics will remain stable when operated in high humidity conditions. Leads require no additional cleaning or processing when used in soldered assembly.



NOTES: A. The centre pin is in electrical contact with the mounting tab.
B. Mounting tab corner profile according to package version.
C. Typical fixing hole centre stand off height according to package version.
Version 1, 18.0 mm. Version 2, 17.6 mm.

MDXXBE

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